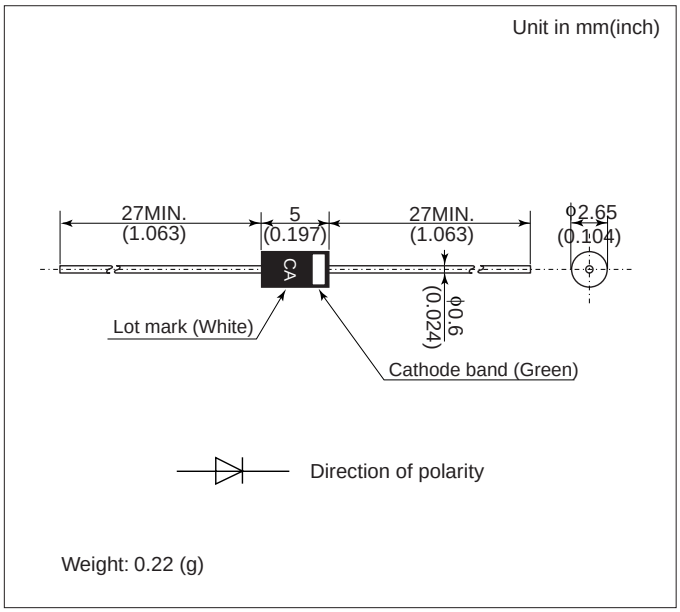
DHM3T30

FEATURES

- High voltage rectification for office equipment.
- Diffused-junction.
- Excellent high temperature output characteristics
  (Small leakage current at high temperature
  and excellent reverse characteristics)

OUTLINE DRAWING



ABSOLUTE MAXIMUM RATINGS

Item	Type		DHM3T30
Repetitive Peak Reverse Voltage*	V_{RRM}	kV	3
Non-Repetitive Peak Reverse Voltage*	V_{RSM}	kV	3.6
Average Forward Current	$I_{F(AV)}$	mA	3 (15.75kHz C-Load)
Surge(Non-Repetitive) Forward Current	I_{FSM}	A	0.5
Operating Junction Temperature	T_j	°C	-40 ~ +120
Storage Temperature	T_{stg}	°C	-40 ~ +120

CHARACTERISTICS (T_C=25°C unless otherwise specified)

Item	Symbols	Units	Min.	Typ.	Max.	Test Conditions
Peak Reverse Current*	I_{RRM}	μA	—	—	2.0	$V_R = V_{RRM}$
Peak Forward Voltage	V_{FM}	V	—	—	10	I_{FM} = 5mAp
Reverse Recovery Time	trr	ns	—	—	100	I_F = 2mA, I_{RP} = 5mA, 1mA recovery

Notes *Diode tested in adequate thermal and dielectric medium.

HITACHI POWER SEMICONDUCTORS

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